

Title (en)

METHOD FOR MAKING A SEMICONDUCTOR PHOTODETECTOR, IN PARTICULAR IN THE LOW-ENERGY UV-X DOMAIN, AND PHOTODETECTOR OBTAINED BY SAID METHOD

Title (de)

HERSTELLUNGSVERFAHREN EINES HALBLEITER-PHOTODETEKTORS, INSBESONDERE FÜR DEN UV-BEREICH UND WEICHE RÖNTGENSTRAHLUNG, UND NACH DIESEM VERFAHREN HERGESTELLTER PHOTODETEKTOR

Title (fr)

PROCEDE DE FABRICATION D'UN PHOTODETECTEUR SEMICONDUCTEUR, NOTAMMENT DANS LE DOMAINE UV-X DE BASSE ENERGIE, ET PHOTODETECTEUR OBTENU PAR CE PROCEDE

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Abstract (en)

[origin: WO03041120A2] The invention concerns a method for making a semiconductor photodetector, in particular in the low-energy UV-X domain, and a photodetector obtained by said method. The invention is characterized in that it consists in making a photodetecting element (22) in photodetecting semiconductor material, said element being provided with electrodes (24, 26). After making the photodetecting element and without impairing the electrodes, it consists in removing a surface layer of the photodetecting semiconductor material to produce a new surface layer having the electrical properties of said material volume.

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H01L 21/00

IPC 8 full level

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